AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning on page 7, line 3, as follows:

It is preferable to form the semiconductor photodetection device so that the dielectric reflecting layer is made of fluoride, oxide or nitride including one or more atoms selected from the group consisting of Si, Al, Mg, Ti, Zr and Ta. Further, it is preferable to form the semiconductor photodetection device so that the close contact electrode is made of Ti or Al. Further, it is preferable to have one or more additional reflecting layers made of dielectric or semiconductor on the dielectric reflecting layer. Further, it is preferable to form the semiconductor photodetection device so that the additional reflecting layers are dielectric layers comprising fluoride, oxide or nitride including one or more atoms selected from the group consisting of Si, Al, Mg, Ti, Zr and Ta, or semiconductor layers including Si or Ge. Further, it is preferable to form the semiconductor photodetection device so that the dielectric reflecting layer has a refractive index of n_1 and the additional reflecting layers has a refractive index of n_2, where $n_2 > n_1$. Further, it is preferable to form the semiconductor photodetection device so that the close contact electrode performs at least partially a function of reflecting incident light. Further, it is preferable to form the semiconductor photodetection device so that the additional reflecting electrode includes transition metal belonging to group 1B or 2B. Further, it is preferable to form the semiconductor photodetection device so that the additional reflecting layer includes one or more atoms selected from the group consisting of Au, Ag and Cu. Further, it is preferable to form the semiconductor photodetection device so that the metal reflecting layer comprises a first metal reflecting layer having a thickness less than the absorption length at the signal light wavelength, and a second metal reflecting

layer on the first metal reflecting layer. Further, it is preferable to form the semiconductor photodetection device so that the first metal reflecting layer includes transition metal belonging to any of groups ~~3A through 8A~~ 3B through 8B and the second metal reflecting layer includes transition metal belonging to group 1B or 2B. Further, it is preferable to form the semiconductor photodetection device so that the first metal reflecting layer includes one or more elements selected from the group consisting of Pt, Ni, TiW and TiN, and the second metal reflecting layer includes one or more atoms selected from the group consisting of Au, Ag and Cu. Further, it is preferable to form the semiconductor photodetection device so that the barrier electrode has a larger area than the contact electrode. Further, it is preferable to form the semiconductor photodetection device so that the contact electrode is a ring shape. Further, it is preferable to form the semiconductor photodetection device so that the contact electrode is formed partially surrounding the dielectric reflecting layer. Further, it is preferable to form the semiconductor photodetection device so that the semiconductor structure is mounted on a semiconductor substrate and the photo-incidence surface is placed on the substrate side of the semiconductor structure. Further, it is preferable to form the semiconductor photodetection device so that the semiconductor structure is mounted on a semiconductor substrate and the photo-incidence surface is placed on a side opposite to the substrate of the semiconductor structure. Further, it is preferable to form the semiconductor photodetection device so that the semiconductor structure further includes a carrier-multiplier layer, and the semiconductor photodetection device is an avalanche photodiode.